

# **SE98**

## DDR memory module temp sensor, 3.3 V

Rev. 04 — 2 February 2009

**Product data sheet** 

## 1. General description

The NXP Semiconductors SE98 measures temperature from –40 °C to +125 °C communicating via the I<sup>2</sup>C-bus/SMBus. It is typically mounted on a Dual In-line Memory Module (DIMM) measuring the DRAM temperature in accordance with the new JEDEC (JC-42.4) *Mobile Platform Memory Module Thermal Sensor Component* specification.

Placing the Temp Sensor (TS) on DIMM allows accurate monitoring of the DIMM module temperature to better estimate the DRAM case temperature ( $T_{case}$ ) to prevent it from exceeding the maximum operating temperature of 85 °C. The chip set throttles the memory traffic based on the actual temperatures instead of the calculated worst-case temperature or the ambient temperature using a temp sensor mounted on the motherboard. There is up to a 30 % improvement in thin and light notebooks that are using one or two 1G SO-DIMM modules, although other memory modules such as in server applications will also see an increase in system performance. Future uses of the TS will include more dynamic control over thermal throttling, the ability to use the Alarm Window to create multiple temperature zones for dynamic throttling and to save processor time by scaling the memory refresh rate.

The TS consists of an Analog-to-Digital Converter (ADC) that monitors and updates its own temperature readings 8 times per second, converts the reading to a digital data, and latches them into the data temperature registers. User-programmable registers, such as Shutdown or Low-power modes and the specification of temperature event and critical output boundaries, provide flexibility for DIMM temperature-sensing applications.

When the temperature changes beyond the specified boundary limits, the SE98 outputs an  $\overline{\text{EVENT}}$  signal. The user has the option of setting the  $\overline{\text{EVENT}}$  output signal polarity as either an active LOW or active HIGH comparator output for thermostat operation, or as a temperature event interrupt output for microprocessor-based systems. The  $\overline{\text{EVENT}}$  output can even be configured as a critical temperature output.

The SE98 supports the industry-standard 2-wire I<sup>2</sup>C-bus/SMBus serial interface. The SMBus TIMEOUT function is supported to prevent system lock-ups. Manufacturer and Device ID registers provide the ability to confirm the identify of the device. Three address pins allow up to eight devices to be controlled on a single bus. To maintain interchangeability with the I<sup>2</sup>C-bus/SMBus interface the electrical specifications are specified with the operating voltage of 3.0 V to 3.6 V.



#### DDR memory module temp sensor, 3.3 V

### 2. Features

### 2.1 General features

- JEDEC (JC-42.4) SO-DIMM temperature sensor
- Optimized for voltage range: 3.0 V to 3.6 V
- Shutdown/Standby current: 8 μA (typ.) and 15 μA (max.)
- 2-wire interface: I<sup>2</sup>C-bus/SMBus compatible, 0 Hz to 400 kHz
- SMBus ALERT and TIMEOUT (programmable)
- Available packages: TSSOP8 and HVSON8

### 2.2 Temperature sensor features

- Temperature-to-Digital converter
- Operating current: 200 μA (typ.) and 250 μA (max.)
- Programmable hysteresis threshold: 0 °C, 1.5 °C, 3 °C, 6 °C
- Over/under/critical temperature EVENT output
- C grade accuracy:
  - $\bullet$  ±1 °C/±2 °C (typ./max.)  $\rightarrow$  +75 °C to +95 °C
  - $\bullet$  ±2 °C/±3 °C (typ./max.)  $\rightarrow$  +40 °C to +125 °C
  - $\bullet$  ±3 °C/±4 °C (typ./max.)  $\rightarrow$  -40 °C to +125 °C

## 3. Applications

- DDR2 and DDR3 memory modules
- Laptops, personal computers and servers
- Enterprise networking
- Hard disk drives and other PC peripherals

## 4. Ordering information

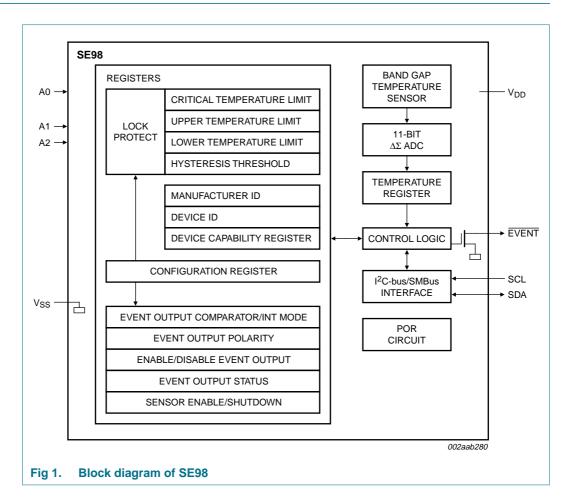
#### Table 1. Ordering information

Type number	Topside	Package					
	mark	Name	Description	Version			
SE98PW	SE98	TSSOP8	plastic thin shrink small outline package; 8 leads; body width 4.4 mm	SOT530-1			
SE98TK	SE98	HVSON8	plastic thermal enhanced very thin small outline package; no leads; 8 terminals; body $3\times3\times0.85$ mm	SOT908-1			

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### DDR memory module temp sensor, 3.3 V

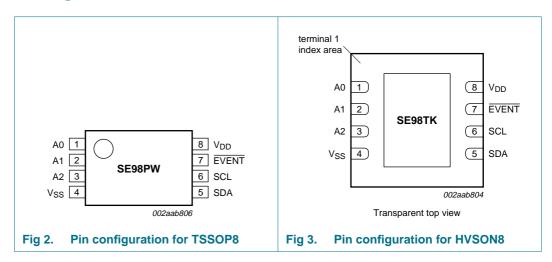
## 5. Block diagram



DDR memory module temp sensor, 3.3 V

## 6. Pinning information

## 6.1 Pinning



## 6.2 Pin description

Table 2. Pin description

Symbol	Pin	Type	Description
A0[1]	1	I	I <sup>2</sup> C-bus/SMBus slave address bit 0
A1	2	I	I <sup>2</sup> C-bus/SMBus slave address bit 1
A2	3	I	I <sup>2</sup> C-bus/SMBus slave address bit 2
$V_{SS}$	4	ground	device ground
SDA	5	I/O	SMBus/I <sup>2</sup> C-bus serial data input/output (open-drain). Must have external pull-up resistor.
SCL	6	I	SMBus/I <sup>2</sup> C-bus serial clock input/output (open-drain). Must have external pull-up resistor.
EVENT	7	0	Thermal alarm output for high/low and critical temperature limit (open-drain). Must have external pull-up resistor.
$V_{DD}$	8	power	device power supply (3.0 V to 3.6 V)

<sup>[1]</sup> In general, application of 10 V on the A0 pin would not damage the pin, but NXP Semiconductors does not guarantee the overvoltage for this pin.

DDR memory module temp sensor, 3.3 V

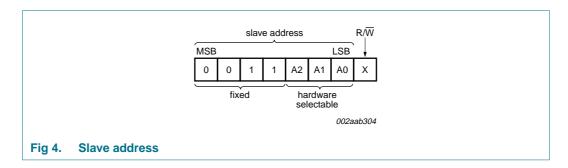
## 7. Functional description

### 7.1 Serial bus interface

The SE98 uses the 2-wire serial bus (I²C-bus/SMBus) to communicate with a host controller. The serial bus consists of a clock (SCL) and data (SDA) signals. The device can operate on either the I²C-bus Standard/Fast mode or SMBus. The I²C-bus Standard-mode is defined to have bus speeds from 0 Hz to 100 kHz, I²C-bus Fast-mode from 0 Hz to 400 kHz, and the SMBus is from 10 kHz to 100 kHz. The host or bus master generates the SCL signal, and the SE98 uses the SCL signal to receive or send data on the SDA line. Data transfer is serial, bidirectional, and is one bit at a time with the Most Significant Bit (MSB) transferred first, and a complete I²C-bus data is 1 byte. Since SCL and SDA are open-drain, pull-up resistors must be installed on these pins.

### 7.2 Slave address

The SE98 uses a 4-bit fixed and 3-bit programmable (A0, A1 and A2) 7-bit slave address that allows a total of eight devices to co-exist on the same bus. The input of each pin is sampled at the start of each I<sup>2</sup>C-bus/SMBus access. The temperature sensor's fixed address is 0011.



#### DDR memory module temp sensor, 3.3 V

## 7.3 EVENT output condition

The EVENT output indicates conditions such as the temperature crossing a predefined boundary. The EVENT modes are very configurable and selected using the configuration register (CONFIG). The interrupt mode or comparator mode is selected using CONFIG[0], using either TCRIT/UPPER/LOWER or TCRIT only temperature bands (CONFIG[2]) as modified by hysteresis (CONFIG[10:9]). The UPPER/LOWER (CONFIG[6]) and TCRIT (CONFIG[7]) bands can be locked. Figure 5 shows an example of the measured temperature versus time, with the corresponding behavior of the EVENT output in each of these modes.

Upon device power-up, the default condition for the EVENT output is high-impedance to prevent spurious or unwanted alarms, but can be later enabled (CONFIG[3]). EVENT output polarity can be set to active HIGH or active LOW (CONFIG[1]). EVENT status can be read (CONFIG[4]) and cleared (CONFIG[5]).

#### Advisory note:

- NXP device: After power-up, bit 3 (1) and bit 2 or bit 0 (leave as 0 or 1) can be set at the same time (e.g., in same byte) but once bit 3 is set (1) then changing bit 2 or bit 0 has no effect on the device operation.
- Competitor device: Does not require that bit 3 be cleared (e.g., set back to (0)) before changing bit 2 or bit 0.
- Work-around: In order to change bit 2 or bit 0 once bit 3 (1) is set, bit 3 (0) must be cleared in one byte and then change bit 2 or bit 0 and reset bit 3 (1) in the next byte.
- SE98B will allow bit 2 or bit 0 to be changed even if bit 3 is set.

If the device enters Shutdown mode (CONFIG[8]) with asserted EVENT output, the output remains asserted during shutdown.

#### 7.3.1 **EVENT** pin output voltage levels and resistor sizing

The EVENT open-drain output is typically pulled up to a voltage level from 0.9 V to 3.6 V with an external pull-up resistor, but there is no real lower limit on the pull-up voltage for the EVENT pin since it is simply an open-drain output. It could be pulled up to 0.1 V and would not affect the output. From the system perspective, there will be a practical limit. That limit will be the voltage necessary for the device monitoring the interrupt pin to detect a HIGH on its input. A possible practical limit for a CMOS input would be 0.4 V. Another thing to consider is the value of the pull-up resistor. When a low supply voltage is applied to the drain (through the pull-up resistor) it is important to use a higher value pull-up resistor, to allow a larger maximum signal swing on the EVENT pin.

### DDR memory module temp sensor, 3.3 V

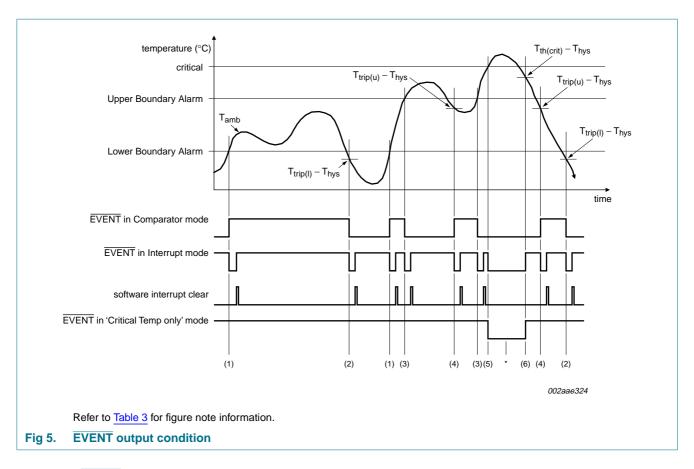


Table 3. **EVENT** output condition

Figure	<b>EVENT</b> output boundary	Ē	VENT outpu	Temperature Register Status bits			
note	conditions	Comparator mode	Interrupt mode	Critical Temp only mode	Bit 15 Above Critical Trip	Bit 14 Above Alarm Window	Bit 13 Below Alarm Window
(1)	$T_{amb} \ge T_{trip(l)}$	Н	L	Н	0	0	0
(2)	$T_{amb} < T_{trip(I)} - T_{hys}$	L	L	Н	0	0	1
(3)	$T_{amb} > T_{trip(u)}$	L	L	Н	0	1	0
(4)	$T_{amb} \leq T_{trip(u)} - T_{hys}$	Н	L	Н	0	0	0
(5)	$T_{amb} \ge T_{th(crit)}$	L	L	L	1	1	0
(6)	$T_{amb} < T_{th(crit)} - T_{hys}$	L	Н	Н	0	1	0

When  $T_{amb} \ge T_{th(crit)}$  and  $T_{amb} < T_{th(crit)} - T_{hys}$  the  $\overline{EVENT}$  output is in Comparator mode and bit 0 of CONFIG ( $\overline{EVENT}$  output mode) is ignored.

7 of 39

#### DDR memory module temp sensor, 3.3 V

#### 7.3.2 **EVENT** thresholds

#### 7.3.2.1 Alarm window

The device provides a comparison window with an UPPER trip point and a LOWER trip point, programmed through the Upper Boundary Alarm Trip register (02h), and Lower Boundary Alarm Trip register (03h). The Upper Boundary Alarm Trip register holds the upper temperature trip point, while the Lower Boundary Alarm Trip register holds the lower temperature trip point as modified by hysteresis as programmed in the Configuration register. When enabled, the EVENT output triggers whenever entering or exiting (crossing above or below) the alarm window.

### Advisory note:

- NXP Device: The EVENT output can be cleared through the Clear EVENT bit or SMBus Alert.
- Competitor Device: The EVENT output can be cleared only through the Clear EVENT bit.
- Work-around: Only clear EVENT output using the EVENT bit.
- There will be no change to the NXP device.

The Upper Boundary Alarm Trip should always be set above the Lower Boundary Alarm Trip.

#### Advisory note:

- NXP device: Requires one conversion cycle (125 ms) after setting the alarm window before comparing the alarm limit with temperature register to ensure that there is correct data in the temperature register before comparing with the Alarm Window and operating EVENT output.
- Competitor devices: Compares the alarm limit with temperature register at any time, so they get the EVENT output immediately when new UPPER or LOWER and Event B3 are set at the same time.
- Work-around: Wait at least 125 ms before enabling EVENT output.
- SE98B will compare alarm window and temperature register immediately after setting.

#### 7.3.2.2 Critical trip

The  $T_{th(crit)}$  temperature setting is programmed in the Critical Alarm Trip register (04h) as modified by hysteresis as programmed in the Configuration register. When the temperature reaches the critical temperature value in this register (and  $\overline{\text{EVENT}}$  is enabled), the  $\overline{\text{EVENT}}$  output asserts and cannot be de-asserted until the temperature drops below the critical temperature threshold. The Event cannot be cleared through the Clear  $\overline{\text{EVENT}}$  bit or SMBus Alert.

The Critical Alarm Trip should always be set above the Upper Boundary Alarm Trip.

#### Advisory note:

 NXP device: Requires one conversion cycle (125 ms) after setting the alarm window before comparing the alarm limit with temperature register to ensure that there is correct data in the temperature register before comparing with the Alarm Window and operating EVENT output.

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#### DDR memory module temp sensor, 3.3 V

- Competitor devices: Compares the alarm limit with temperature register at any time, so they get the EVENT output immediately when new T<sub>th(crit)</sub> and Event B3 are set at the same time.
- Work-around: Wait at least 125 ms before enabling EVENT output. Intel will
  change Nehalem BIOS so that T<sub>th(crit)</sub> is set for more than 125 ms before Event B3
  is enabled and Event value is checked.
  - 1. Set T<sub>th(crit)</sub>.
  - 2. Doing something else (make sure that exceeds 125 ms).
  - 3. Enable the  $\overline{\text{EVENT}}$  output (B3 = 1).
  - 4. Wait 20 μs.
  - 5. Read Event value.
- SE98B will compare alarm window and temperature register immediately after setting.

#### 7.3.3 Event operation modes

#### 7.3.3.1 Comparator mode

In comparator mode, the EVENT output behaves like a window-comparator output that asserts when the temperature is outside the window (e.g., above the value programmed in the Upper Boundary Alarm Trip register or below the value programmed in the Lower Boundary Alarm Trip register or above the Critical Alarm Trip resister if T<sub>th(crit)</sub> only is selected). Reads/writes on the registers do not affect the EVENT output in comparator mode. The EVENT signal remains asserted until the temperature goes inside the alarm window or the window thresholds are reprogrammed so that the current temperature is within the alarm window.

The comparator mode is useful for thermostat-type applications, such as turning on a cooling fan or triggering a system shutdown when the temperature exceeds a safe operating range.

#### 7.3.3.2 Interrupt mode

In interrupt mode,  $\overline{\text{EVENT}}$  asserts whenever the temperature crosses an alarm window threshold. After such an event occurs, writing a 1 to the Clear  $\overline{\text{EVENT}}$  bit in the configuration register de-asserts the  $\overline{\text{EVENT}}$  output until the next trigger condition occurs.

In interrupt mode,  $\overline{\text{EVENT}}$  asserts when the temperature crosses the alarm upper boundary. If the  $\overline{\text{EVENT}}$  output is cleared and the temperature continues to increase until it crosses the critical temperature threshold,  $\overline{\text{EVENT}}$  asserts again. Because the temperature is greater than the critical temperature threshold, a Clear  $\overline{\text{EVENT}}$  command does not clear the  $\overline{\text{EVENT}}$  output. Once the temperature drops below the critical temperature,  $\overline{\text{EVENT}}$  de-asserts immediately.

#### Advisory note:

 NXP device: If the EVENT output is not cleared before the temperature goes above the critical temperature threshold EVENT de-asserts immediately when temperature drops below the critical temperature.

#### DDR memory module temp sensor, 3.3 V

- Competitor devices: If the EVENT output is not cleared before or when the temperature is in the critical temperature threshold, EVENT will remain asserted after the temperature drops below the critical temperature until a Clear EVENT command.
- Work-around: Always clear the EVENT output before temperature exceeds the critical temperature.
- SE98B will keep EVENT asserted after the temperature drops below the critical temperature until a Clear EVENT command de-asserts EVENT.

#### 7.4 Conversion rate

The conversion time is the amount of time required for the ADC to complete a temperature measurement for the local temperature sensor. The conversion rate is the inverse of the conversion period which describes the number of cycles the temperature measurement completes in one second—the faster the conversion rate, the faster the temperature reading is updated. The SE98's conversion rate is at least 8 Hz or 125 ms.

## 7.5 Power-up default condition

After power-on, the SE98 is initialized to the following default condition:

- Starts monitoring local sensor
- EVENT register is cleared—EVENT output is pulled HIGH by external pull-ups
- EVENT hysteresis is defaulted to 0 °C
- Command pointer is defaulted to '00h'
- Critical Temp, Alarm Temperature Upper and Lower Boundary Trip register are defaulted to 0 °C
- Capability register is defaulted to '0015h'
- Operational mode: comparator
- SMBus register is defaulted to '00h'

#### 7.6 Device initialization

SE98 temperature sensors have programmable registers, which, upon power-up, default to zero. The open-drain EVENT output is default to being disabled, comparator mode and active LOW. The alarm trigger registers default to being unprotected. The configuration registers, upper and lower alarm boundary registers and critical temperature window are defaulted to zero and need to be programmed to the desired values. SMBus TIMEOUT feature defaults to being enabled and can be programmed to disable. These registers are required to be initialized before the device can properly function. Except for the SPD, which does not have any programmable registers, and does not need to be initialized.

<u>Table 4</u> shows the default values and the example value to be programmed to these registers.

0000h

#### DDR memory module temp sensor, 3.3 V

SMBus register = no change

Table 4.	Registers to be i	nitialized	
Register	Default value	Example value	Description
01h	0000h	0209h	<ul> <li>Configuration register</li> <li>hysteresis = 1.5 °C</li> <li>EVENT output = Interrupt mode</li> <li>EVENT output is enabled</li> </ul>
02h	0000h	0550h	Upper Boundary Alarm Trip register = 85 °C
03h	0000h	1F40h	Lower Boundary Alarm Trip register = −20 °C
04h	0000h	05F0h	Critical Alarm Trip register = 95 °C

Table 4. Registers to be initialized

0000h

#### 7.7 SMBus time-out

22h

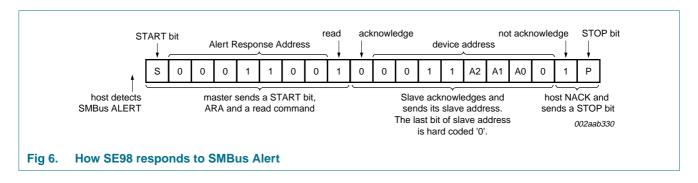
The SE98 supports the SMBus time-out feature. If the host holds SCL LOW between 25 ms and 35 ms, the SE98 would reset its internal state machine to the bus idle state to prevent the system bus hang-up. This feature is turned on by default. The SMBus time-out is disabled by writing a logic 1 to bit 7 of register 22h.

**Remark:** When SMBus time-out is enabled, the I<sup>2</sup>C-bus minimum bus speed is limited by the SMBus time-out timer, and goes down to only 10 kHz.

### 7.8 SMBus Alert

The SE98 supports SMBus Alert when it is programmed for the Interrupt mode and when the EVENT polarity bit is set to logic 0. The EVENT pin can be ANDed with other EVENT or ALERT signals from other slave devices to signal their intention to communicate with the host controller. When the host detects EVENT or ALERT signal LOW, it issues an Alert Response Address (ARA) to which a slave device would respond with its address. When there are multiple slave devices generating an Alert the SE98 performs bus arbitration. If it wins the bus, it responds to the ARA and then clears the EVENT pin.

**Remark:** Either in comparator mode or when the SE98 crosses the critical temperature, the host must also read the  $\overline{\text{EVENT}}$  status bit and provide remedy to the situation by bringing the temperature to within the alarm window or below the critical temperature if that bit is set. Otherwise, the  $\overline{\text{EVENT}}$  pin will not get de-asserted.



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#### DDR memory module temp sensor, 3.3 V

## 7.9 SMBus/I<sup>2</sup>C-bus interface

The data registers in this device are selected by the Pointer register. At power-up, the Pointer register is set to '00', the location for the Capability register. The Pointer register latches the last location it was set to. Each data register falls into one of three types of user accessibility:

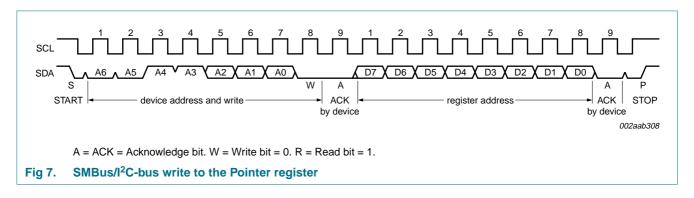
- Read only
- Write only
- Write/Read same address.

A 'write' to this device will always include the address byte and the pointer byte. A write to any register other than the Pointer register requires two data bytes.

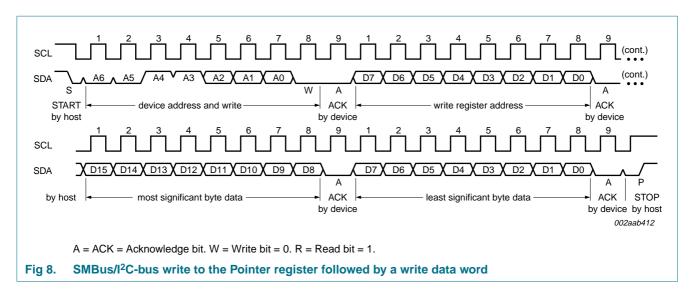
Reading this device can take place either of two ways:

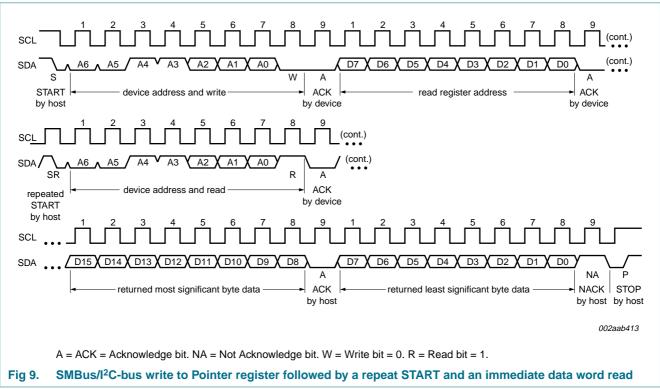
- If the location latched in the Pointer register is correct (most of the time it is expected
  that the Pointer register will point to one of the Temperature register (as it will be the
  data most frequently read), then the read can simply consist of an address byte,
  followed by retrieving the two data bytes.
- If the Pointer register needs to be set, then an address byte, pointer byte, repeat START, and another address byte will accomplish a read.

The data byte has the most significant bit first. At the end of a read, this device can accept either Acknowledge (ACK) or No Acknowledge (NACK) from the Master (No Acknowledge is typically used as a signal for the slave that the Master has read its last byte). It takes this device 125 ms to measure the temperature. Refer to the timing diagrams in <a href="Figure 7">Figure 8</a>, Figure 9 and <a href="Figure 10">Figure 10</a> on how to program the device.

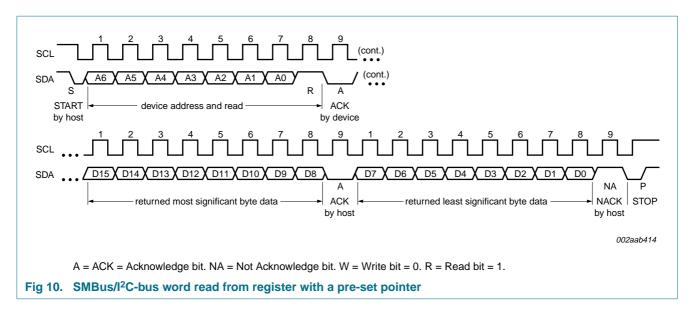


### DDR memory module temp sensor, 3.3 V





#### DDR memory module temp sensor, 3.3 V



### 7.10 Hot plugging

The SE98 can be used in hot plugging applications. Internal circuitry prevents damaging current backflow through the device when it is powered down, but with the I<sup>2</sup>C-bus, EVENT or address pins still connected. The open-drain SDA and EVENT pins (SCL and address pins are input only) effectively places the outputs in a high-impedance state during power-up and power-down, which prevents driver conflict and bus contention. The 50 ns noise filter will filter out any insertion glitches from the state machine, which is very robust and not prone to false operation.

The device needs a proper power-up sequence to reset itself, not only for the device I<sup>2</sup>C-bus and I/O initial states, but also to load specific pre-defined data or calibration data into its operational registers. The power-up sequence should occur correctly with a fast ramp rate and the I<sup>2</sup>C-bus active. The SE98 might not respond immediately after power-up, but it should not damage the part if the power-up sequence is abnormal. If the SCL line is held LOW, the part will not exit the power-on reset mode since the part is held in reset until SCL is released.

DDR memory module temp sensor, 3.3 V

## 8. Register descriptions

## 8.1 Register overview

This section describes all the registers used in the SE98. The registers are used for latching the temperature reading, storing the low and high temperature limits, configuring, the hysteresis threshold and the ADC, as well as reporting status. The device uses the Pointer register to access these registers. Read registers, as the name implies, are used for read only, and the write registers are for write only. Any attempt to read from a write-only register will result in reading zeroes. Writing to a read-only register will have no effect on the read even though the write command is acknowledged. The Pointer register is an 8-bit register. All other registers are 16-bit.

Table 5. Register summary

•	•	
Address	POR state	Register name
n/a	n/a	Pointer register
00h	0015h	Capability register C grade = 0015h
01h	0000h	Configuration register
02h	0000h	Upper Boundary Alarm Trip register
03h	0000h	Lower Boundary Alarm Trip register
04h	0000h	Critical Alarm Trip register
05h	n/a	Temperature register
06h	1131h	Manufacturer ID register
07h	A101h	Device ID/Revision register
08h to 21h	0000h	reserved registers
22h	0000h	SMBus register
23h to FFh	0000h	reserved registers

A write to reserved registers my cause unexpected results which may result in requiring a reset by removing and re-applying its power.

## DDR memory module temp sensor, 3.3 V

## 8.2 Capability register (00h, 16-bit read-only)

Table 6. Capability register (address 00h) bit allocation

Bit	15	14	13	12	11	10	9	8
Symbol				RFU	[10:3]			
Reset	0	0	0	0	0	0	0	0
Access	R	R	R	R	R	R	R	R
Bit	7	6	5	4	3	2	1	0
Symbol		RFU[2:0]		TRE	S[1:0]	WRNG	HACC	BCAP
Reset	0	0	0	1	0	1	0	1
Access	R	R	R	R	R	R	R	R

Table 7. Capability register (address 00h) bit description

Bit	Symbol	Description
15:5	RFU	Reserved for future use. Must be zero.
4:3	TRES	Temperature resolution. 10 — 0.125 °C LSB (11-bit)
2	WRNG	Wider range.  1 — can read temperatures below 0 °C and set sign bit accordingly
1	HACC	Higher accuracy (set during manufacture).  0 — C grade accuracy
0	BCAP	Basic capability.  1 — has Alarm and Critical Trips interrupt capability.

#### DDR memory module temp sensor, 3.3 V

## 8.3 Configuration register (01h, 16-bit read/write)

Table 8. Configuration register (address 01h) bit allocation

Bit	15	14	13	12	11	10	9	8
Symbol			RFU			HEN	I[1:0]	SHMD
Default	0	0	0	0	0	0	0	0
Access	R	R	R	R	R	R/W	R/W	R/W
Bit	7	6	5	4	3	2	1	0
Symbol	CTLB	AWLB	CEVNT	ESTAT	EOCTL	CVO	EP	EMD
Default	0	0	0	0	0	0	0	0
Access	R/W	R/W	R/W	R/W	R/W	R/W	R/W	R/W

Table 9.	Configuration register (address 01h) bit description					
Bit	Symbol	Description				
15:11	RFU	reserved for future use; must be '0'.				
10:9	HEN	Hysteresis Enable				
		00 — Disable hysteresis (default)				
		01 — Enable hysteresis at 1.5 °C				
		10 — Enable hysteresis at 3 °C				
		11 — Enable hysteresis at 6 °C				
		When enabled, hysteresis is applied to temperature movement around trigger points. For example, consider the behavior of the 'Above Alarm Window' bit (bit 14 of the Temperature register) when the hysteresis is set to 3 °C. As the temperature rises, bit 14 will be set to 1 (temperature is above the alarm window) when the Temperature register contains a value that is greater than the value in the Alarm Temperature Upper Boundary register. If the temperature decreases, bit 14 will remain set until the measured temperature is less than or equal to the value in the Alarm Temperature				

Upper Boundary register minus 3 °C. (Refer to Figure 5 and Table 10). Similarly, the 'Below Alarm Window' bit (bit 13 of the Temperature register) will be set to 0 (temperature is equal to or above the Alarm Window Lower Boundary Trip register) when the value in the Temperature register is equal to or greater than the value in the Alarm Temperature Lower Boundary register. As the temperature decreases, bit 13 will be set to 1 when the value in the Temperature register is equal to or less than the value in the Alarm Temperature Lower Boundary register minus 3 °C. Note that hysteresis is also applied to  $\overline{\text{EVENT}}$  pin functionality.

When either of the lock bits is set, these bits cannot be altered.

#### 8 SHMD

Shutdown Mode.

0 — Enabled Temperature Sensor (default)

1 — Disabled Temperature Sensor

When shut down, the thermal sensor diode and Analog-to-Digital Converter (ADC) are disabled to save power, no events will be generated. When either of the lock bits is set, this bit cannot be set until unlocked. However, it can be cleared at any time.

## DDR memory module temp sensor, 3.3 V

Table 9. Co	nfiguration	register	(address C	)1h) bit	description	continued
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D:4	Cumala al	Description
Bit	Symbol	Description
7	CTLB	Critical Trip Lock bit.
		<ul> <li>0 — Critical Alarm Trip register is not locked and can be altered (default).</li> </ul>
		<ol> <li>Critical Alarm Trip register settings cannot be altered.</li> </ol>
		This bit is initially cleared. When set, this bit will return a 1, and remains locked until cleared by internal Power-on reset. This bit can be written with a single write and do not require double writes.
6	AWLB	Alarm Window Lock bit.
		<ul> <li>Upper and Lower Alarm Trip registers are not locked and can be altered (default).</li> </ul>
		1 — Upper and Lower Alarm Trip registers setting cannot be altered.
		This bit is initially cleared. When set, this bit will return a 1 and remains locked until cleared by internal power-on reset. This bit can be written with a single write and does not require double writes.
5	CEVNT	Clear EVENT (write only).
		0 — No effect (default).
		1 — Clears active EVENT in Interrupt mode. Writing to this register has no effect in Comparator mode.
		When read, this register always returns zero.
4	ESTAT	EVENT Status (read only).
		$0 - \overline{\text{EVENT}}$ output condition is not being asserted by this device (default).
		1 — EVENT output pin is being asserted by this device due to Alarm Window or Critical Trip condition.
		The actual event causing the event can be determined from the Read Temperature register. Interrupt Events can be cleared by writing to the 'Clear EVENT' bit. Writing to this bit will have no effect.
3	EOCTL	EVENT Output Control.
		0 — EVENT output disabled (default).
		1 — EVENT output enabled.
		When either of the lock bits is set, this bit cannot be altered until unlocked.
2	CVO	Critical Event Only.
		0 — EVENT output on Alarm or Critical temperature event (default)
		1 — EVENT only if temperature is above the value in the critical temperature register
		When the Critical Trip or Alarm Window lock bit is set, this bit cannot be altered until unlocked.
		Advisory note:
		<ul> <li>JEDEC specification requires only the Alarm Window lock bit to be set.</li> </ul>
		<ul> <li>Workaround: Clear both Critical Trip and Alarm Window lock bits.</li> </ul>
		<ul> <li>Future 1.7 V to 3.6 V SE98B will require only the Alarm Window lock bit to be set.</li> </ul>

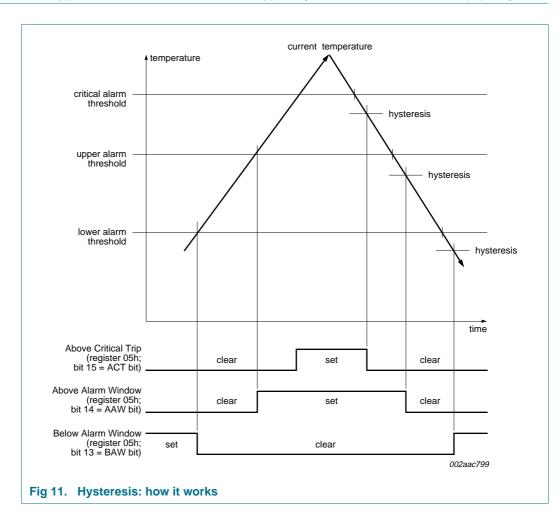
## DDR memory module temp sensor, 3.3 V

Table 9. Configuration register (address 01h) bit description ...continued

Bit	Symbol	Description
1	EP	EVENT Polarity.
		0 — active LOW (default).
		1 — active HIGH. When either of the alarm or critical lock bits is set, this bit cannot be altered until unlocked.
0	EMD	EVENT Mode.
		0 — comparator output mode (default)
		1 — interrupt mode
		When either of the alarm or critical lock bits is set, this bit cannot be altered until unlocked.

Table 10. Hysteresis enable

Action	Below Alarm V	Vindow Bit (bit 13)	Above Alarm W	/indow Bit (bit 14)	Above Critical Trip bit (bit 15)					
	Temperature slope	Threshold temperature	Temperature slope	Temperature	Temperature slope	Threshold temperature				
sets	falling	$T_{trip(I)} - T_{hys}$	rising	$T_{trip(u)}$	rising	T <sub>th(crit)</sub>				
clears	rising	$T_{trip(I)}$	falling	$T_{trip(u)} - T_{hys}$	falling	$T_{th(crit)} - T_{hys}$				



## DDR memory module temp sensor, 3.3 V

## 8.4 Temperature format

The 16-bit value used in the following Trip Point Set and Temperature Read-Back registers is 2's complement with the Least Significant Bit (LSB) equal to 0.0625 °C. For example:

- A value of 019Ch will represent 25.75 °C
- A value of 07C0h will represent 124 °C
- A value of 1E64h will represent -25.75 °C.

The resolution is 0.125  $^{\circ}$ C. The unused LSB (bit 0) is set to '0'. Bit 11 will have a resolution of 128  $^{\circ}$ C.

The upper 3 bits of the temperature register indicate Trip Status based on the current temperature, and are not affected by the status of the  $\overline{\text{EVENT}}$  output.

<u>Table 11</u> lists the examples of the content of the temperature data register for positive and negative temperature for two scenarios of status bits: status bits = 000b and status bits = 111b.

Table 11. Degree Celsius and Temperature Data register

Temperature	Content of Temperature Data register							
	Status bits = 000b	Status bits = 111b						
	Binary	Hex	Binary	Hex				
+125 °C	000 0 01111101 000 0	07D0h	111 0 011111101 000 0	E7D0h				
+25 °C	000 0 00011001 000 0	0190h	111 0 00011001 000 0	E190h				
+1 °C	000 0 00000001 000 0	0010h	111 0 00000001 000 0	E010h				
+0.25 °C	000 0 00000000 010 0	0004h	111 0 00000000 010 0	E004h				
+0.125 °C	000 0 00000000 001 0	0002h	111 0 00000000 001 0	E002h				
0 °C	000 0 00000000 000 0	0000h	111 0 00000000 000 0	E000h				
–0.125 °C	000 1 11111111 111 0	1FFEh	111 1 11111111 111 0	FFFEh				
–0.25 °C	000 1 11111111 110 0	1FFCh	111 1 11111111 110 0	FFFCh				
−1 °C	000 1 11111111 000 0	1FF0h	111 1 11111111 000 0	FFF0h				
–20 °C	000 1 11110100 000 0	1F40h	111 1 11110100 000 0	FF40h				
–25 °C	000 1 11100111 000 0	1E70h	111 1 11100111 000 0	FE70h				
–55 °C	000 1 11001001 000 0	1C90h	111 1 11001001 000 0	FC90h				

### DDR memory module temp sensor, 3.3 V

## 8.5 Temperature Trip Point registers

## 8.5.1 Upper Boundary Alarm Trip register (16-bit read/write)

The value is the upper threshold temperature value for Alarm mode. The data format is 2's complement with bit 2 = 0.25 °C. 'RFU' bits will always report zero. Interrupts will respond to the presently programmed boundary values. If boundary values are being altered in-system, it is advised to turn off interrupts until a known state can be obtained to avoid superfluous interrupt activity.

Table 12. Upper Boundary Alarm Trip register bit allocation

	- 11 15 -			3				
Bit	15	14	13	12	11	10	9	8
Symbol		RFU		SIGN		UBT	[9:6]	
Reset	0	0	0	0	0	0	0	0
Access	R	R	R	R/W	R/W	R/W	R/W	R/W
Bit	7	6	5	4	3	2	1	0
Symbol			UBT	[5:0]			RI	FU
Reset	0	0	0	0	0	0	0	0
Access	R/W	R/W	R/W	R/W	R/W	R/W	R	R

Table 13. Upper Boundary Alarm Trip register bit description

15:13 RFU reserved; always 0  12 SIGN Sign (MSB)  11:2 UBT Upper Boundary Alarm Trip Temperature (LSB = 0.25 °C)	Bit	Symbol	Description
11:2 UBT Upper Boundary Alarm Trip Temperature (LSB = 0.25 °C)	15:13	RFU	reserved; always 0
opportunities, which is the control of	12	SIGN	Sign (MSB)
	11:2	UBT	Upper Boundary Alarm Trip Temperature (LSB = 0.25 °C)
1:0 RFU reserved; always 0	1:0	RFU	reserved; always 0

#### DDR memory module temp sensor, 3.3 V

## 8.5.2 Lower Boundary Alarm Trip register (16-bit read/write)

The value is the lower threshold temperature value for Alarm mode. The data format is 2's complement with bit 2 = 0.25 °C. RFU bits will always report zero. Interrupts will respond to the presently programmed boundary values. If boundary values are being altered in-system, it is advised to turn off interrupts until a known state can be obtained to avoid superfluous interrupt activity.

Table 14. Lower Boundary Alarm Trip register bit allocation

			•	•				
Bit	15	14	13	12	11	10	9	8
Symbol		RFU		SIGN		LBT	[9:6]	
Reset	0	0	0	0	0	0	0	0
Access	R	R	R	R/W	R/W	R/W	R/W	R/W
Bit	7	6	5	4	3	2	1	0
Symbol			LBT	[5:0]			RI	FU
Reset	0	0	0	0	0	0	0	0
Access	R/W	R/W	R/W	R/W	R/W	R/W	R	R

Table 15. Lower Boundary Alarm Trip register bit description

Bit	Symbol	Description
15:13	RFU	reserved; always 0
12	SIGN	Sign (MSB)
11:2	LBT	Lower Boundary Alarm Trip Temperature (LSB = 0.25 °C)
1:0	RFU	reserved; always 0

## 8.5.3 Critical Alarm Trip register (16-bit read/write)

The value is the critical temperature. The data format is 2's complement with bit 2 = 0.25 °C. RFU bits will always report zero.

Table 16. Lower Boundary Alarm Trip register bit allocation

Bit	15	14	13	12	11	10	9	8
Symbol		RFU		SIGN		CT[	9:6]	
Reset	0	0	0	0	0	0	0	0
Access	R	R	R	R/W	R/W	R/W	R/W	R/W
Bit	7	6	5	4	3	2	1	0
Symbol			CT	[5:0]			RI	FU
Reset	0	0	0	0	0	0	0	0
Access	R/W	R/W	R/W	R/W	R/W	R/W	R	R

Table 17. Critical Alarm Trip register bit description

		<u> </u>
Bit	Symbol	Description
15:13	RFU	reserved; always 0
12	SIGN	Sign (MSB)
11:2	CT	Critical Alarm Trip Temperature (LSB = 0.25 °C)
1:0	RFU	reserved; always 0

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### DDR memory module temp sensor, 3.3 V

## 8.6 Temperature register (16-bit read-only)

Table 18. Temperature register bit allocation

Bit	15	14	13	12	11	10	9	8
Symbol	ACT	AAW	BAW	SIGN		TEMP	[10:7]	
Reset	0	0	0	0	0	0	0	0
Access	R	R	R	R	R	R	R	R
Bit	7	6	5	4	3	2	1	0
Symbol				TEMP[6:0]				RFU
Reset	0	0	0	0	0	0	0	0
Access	R	R	R	R	R	R	R	R

Table 19. Temperature register bit description

Bit	Symbol	Description
15	ACT	Above Critical Trip.
		0 — temperature is below the Critical Alarm Trip register setting
		1 — temperature is equal to or above the Critical Alarm Trip register setting
14	AAW	Above Alarm Window.
		0 — temperature is equal to or below the Upper Boundary Alarm Trip register
		1 — temperature is above the Alarm window
13	BAW	Below Alarm Window.
		0 — temperature is equal to or above the Lower Boundary Alarm Trip register
		1 — temperature is below the Alarm window
12	SIGN	Sign bit.
		0 — positive temperature value
		1 — negative temperature value
11:1	TEMP	Temperature Value (2's complement). (LSB = 0.125 °C)
0	RFU	reserved; always 0

## 8.7 Manufacturer's ID register (16-bit read-only)

The manufacture's ID matches that assigned to NXP Semiconductors PCI-SIG (1131h), and is intended for use to identify the manufacturer of the device.

Table 20. Manufacturer's ID register bit allocation

Bit	15	14	13	12	11	10	9	8
Symbol				Manufac	turer ID			
Reset	0	0	0	1	0	0	0	1
Access	R	R	R	R	R	R	R	R
Bit	7	6	5	4	3	2	1	0
Symbol				(conti	nued)			
Reset	0	0	1	1	0	0	0	1
Access	R	R	R	R	R	R	R	R

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## DDR memory module temp sensor, 3.3 V

## 8.8 Device ID register

The device ID and device revision are A1h and 00h, respectively.

Table 21. Device ID register bit allocation

Bit	15	14	13	12	11	10	9	8
Symbol				Devi	ce ID			
Reset	1	0	1	0	0	0	0	1
Access	R	R	R	R	R	R	R	R
Bit	7	6	5	4	3	2	1	0
Symbol				Device	revision			
Reset	0	0	0	0	0	0	0	1
Access	R	R	R	R	R	R	R	R

## 8.9 SMBus register

Table 22. SMBus Time-out register bit allocation

Bit	15	14	13	12	11	10	9	8
Symbol				RF	U			
Reset	0	0	0	0	0	0	0	0
Access	R	R	R	R	R	R	R	R
Bit	7	6	5	4	3	2	1	0
Symbol	STMOUT			RI	FU			SALRT
Reset	0	0	0	0	0	0	0	0
Access	R/W	R	R	R	R	R	R	R/W

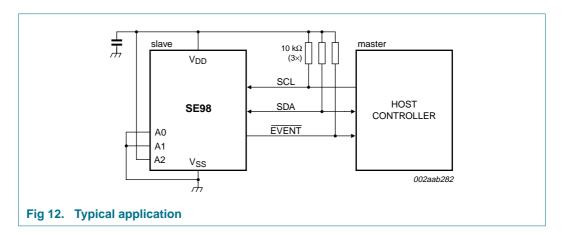
Table 23. SMBus Time-out register bit description

Bit	Symbol	Description
15:8	RFU	reserved; always 0
7	STMOUT	SMBus time-out.  0 — SMBus time-out is enabled (default)  1 — disable SMBus time-out  When either of the lock bits is set, this bit cannot be altered until unlocked.
6:1	RFU	reserved; always 0
0	SALRT	SMBus Alert.  0 — SMBus Alert is enabled (default)  1 — disable SMBus Alert  When either of the lock bits is set, this bit cannot be altered until unlocked.

DDR memory module temp sensor, 3.3 V

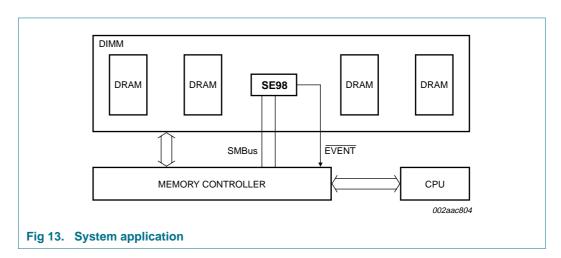
## 9. Application design-in information

In a typical application, the SE98 behaves as a slave device and interfaces to the master (or host) via the SCL and SDA lines. The host monitors the  $\overline{\text{EVENT}}$  output pin, which is asserted when the temperature reading exceeds the programmed values in the alarm registers. The A0, A1 and A2 pins are directly connected to the shared SPD's A0, A1 and A2 pins, otherwise they must be pulled HIGH or LOW. The SDA and SCL serial interface pins are open-drain and require pull-up resistors, and are able to sink a maximum current of 3 mA with a voltage drop less than 0.4 V. Typical pull-up values for SCL and SDA are 10 k $\Omega$ , but the resistor values can be changed in order to meet the rise time requirement if the capacitance load is too large due to routing, connectors, or multiple components sharing the same bus.



### 9.1 SE98 in memory module application

<u>Figure 13</u> shows the SE98 being placed in the memory module application. The SE98 is centered in the memory module to provide the function to monitor the temperature of the DRAM. In the event of overheat, the SE98 triggers the <u>EVENT</u> output and the memory controller can throttle the memory bus to slow the DRAM, or the CPU can increase the refresh rate for the DRAM. The memory controller can also read the SE98 and watch the DRAM thermal behavior.



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#### DDR memory module temp sensor, 3.3 V

### 9.2 Layout consideration

The SE98 does not require any additional components other than the host controller to measure temperature. A 0.1  $\mu$ F bypass capacitor between the V<sub>DD</sub> and V<sub>SS</sub> pins is located as close as possible to the power and ground pins for noise protection.

## 9.3 Thermal considerations

In general, self-heating is the result of power consumption and not a concern, especially with the SE98, which consumes very low power. In the event the SDA and  $\overline{\text{EVENT}}$  pins are heavily loaded with small pull-up resistor values, self-heating affects temperature accuracy by approximately 0.5 °C.

Equation 1 is the formula to calculate the effect of self-heating:

$$T\Delta = R_{th(i-a)} \times [(V_{DD} \times I_{DD}) + (V_{OL1} \times I_{OL1}) + (V_{OL2} \times I_{OL2})]$$
(1)

where:

 $T\Delta = T_i - T_{amb}$ 

 $T_i$  = junction temperature

 $T_{amb}$  = ambient temperature

 $R_{th(i-a)}$  = package thermal resistance

V<sub>OL1</sub> = SDA output low voltage

 $V_{OL2} = \overline{EVENT}$  output low voltage

I<sub>OL1</sub> = SDA output current LOW

 $I_{OL2} = \overline{\text{EVENT}}$  output current LOW.

## 10. Limiting values

Table 24. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{DD}$	supply voltage		-0.3	+4.2	V
$V_n$	voltage on any other pin	SDA, SCL, $\overline{EVENT}$ pins	-0.3	+4.2	V
$V_{A0}$	voltage on pin A0	overvoltage input; A0 pin	<u>[1]</u> –0.3	+10	V
I <sub>sink</sub>	sink current	at SDA, SCL, $\overline{\text{EVENT}}$ pins	-1	+50.0	mA
V <sub>esd</sub>	electrostatic discharge	HBM	-	2500	V
	voltage	MM	-	250	V
		CDM	-	1000	V
$T_{j(max)}$	maximum junction temperature		-	150	°C
T <sub>stg</sub>	storage temperature		-65	+165	°C

<sup>[1]</sup> In general, application of 10 V on the A0 pin would not damage the pin, but NXP Semiconductors does not guarantee the overvoltage for this pin.

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## DDR memory module temp sensor, 3.3 V

## 11. Characteristics

Table 25. Characteristics

 $V_{DD}$  = 3.0 V to 3.6 V;  $T_{amb}$  = -40 °C to +125 °C; unless otherwise specified.

	,	•				
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
T <sub>lim(acc)</sub>	temperature limit accuracy	C grade temperature accuracy; $V_{DD}$ = 3.3 V $\pm$ 10 %				
		T <sub>amb</sub> = 75 °C to 95 °C	-2.0	< ±1	+2.0	°C
		T <sub>amb</sub> = 40 °C to 125 °C	-3.0	< ±2	+3.0	°C
		$T_{amb} = -40  ^{\circ}\text{C} \text{ to } +125  ^{\circ}\text{C}$	-4.0	< ±3	+4.0	°C
T <sub>res</sub>	temperature resolution		-	0.25	-	°C
I <sub>DD(AV)</sub>	average supply current		-	-	250	μΑ
I <sub>DD(stb)</sub>	standby supply current	SMBus inactive	-	8	15	μΑ
T <sub>conv</sub>	conversion period		-	100	-	ms
E <sub>f(conv)</sub>	conversion rate error	percentage error in programmed data	-30	-	+30	%
IL	leakage current	on A0, A1, A2 pins	-	1	-	μΑ
$V_{DD}$	supply voltage		3.0	3.3	3.6	V

#### Table 26. SMBus DC characteristics

 $V_{DD} = 3.0 \text{ V}$  to 3.6 V;  $T_{amb} = -40 \,^{\circ}\text{C}$  to  $+120 \,^{\circ}\text{C}$ ; unless otherwise specified. These specifications are guaranteed by design.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V <sub>IH</sub>	HIGH-level input voltage	SCL, SDA; $V_{DD} = 3.0 \text{ V}$ to $3.6 \text{ V}$	2.2	-	-	V
V <sub>IL</sub>	LOW-level input voltage	SCL, SDA; $V_{DD} = 3.0 \text{ V}$ to 3.6 V	-	-	0.8	V
I <sub>OL(sink)</sub> EVENT	LOW-level output sink current on pin EVENT	$V_{OL} = 0.4 V$	1	-	-	mA
I <sub>OL(sink)(SDA)</sub>	LOW-level output sink current on pin SDA	V <sub>OL</sub> = 0.6 V	6	-	-	mA
$I_{LOH}$	HIGH-level output leakage current	$V_{OH} = V_{DD}$	-	-	1.0	μΑ
I <sub>LIH</sub>	HIGH-level input leakage current	$V_I = V_{DD}$ or $V_{SS}$	-1.0	-	+1.0	μΑ
I <sub>LIL</sub>	LOW-level input leakage current	$V_I = V_{DD}$ or $V_{SS}$	-1.0	-	+1.0	μΑ
C <sub>i</sub>	input capacitance	SCL, SDA pins	-	5	10	pF

### DDR memory module temp sensor, 3.3 V

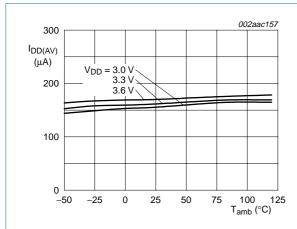


Fig 14. Supply current versus temperature

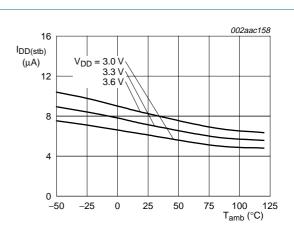


Fig 15. Standby supply current versus temperature

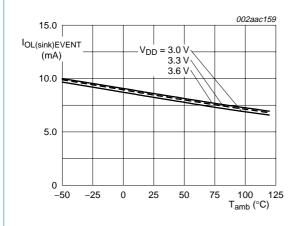


Fig 16. EVENT sink current at 0.4 V versus temperature

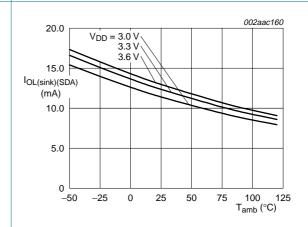
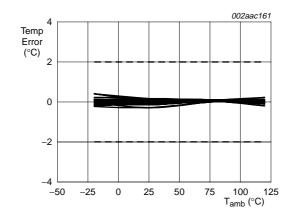


Fig 17. EVENT sink current at 0.6 V versus temperature



Sample of 25 devices at  $V_{DD} = 3.3 \text{ V}$ 

Fig 18. Temperature Error versus temperature

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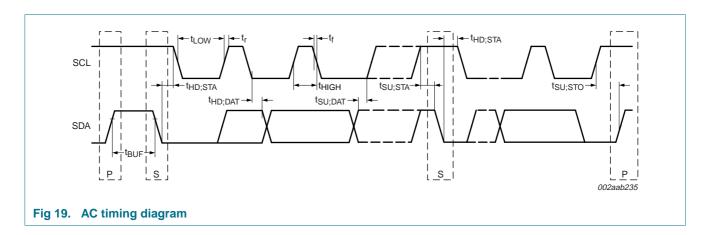
### DDR memory module temp sensor, 3.3 V

#### Table 27. SMBus AC characteristics

 $V_{DD} = 3.0 \text{ V}$  to 3.6 V;  $T_{amb} = -40 \,^{\circ}\text{C}$  to  $+120 \,^{\circ}\text{C}$ ; unless otherwise specified. These specifications are guaranteed by design. The AC specifications fully meet or exceed SMBus 2.0 specifications, but allow the bus to interface with the  $I^2\text{C}$ -bus from DC to 400 kHz.

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
$f_{SCL}$	SCL clock frequency			0	-	400	kHz
$t_{LOW}$	LOW period of the SCL clock	10 % to 10 %		1.3	-	-	μs
t <sub>HIGH</sub>	HIGH period of the SCL clock	90 % to 90 %		0.6	-	-	μs
t <sub>BUF</sub>	bus free time between a STOP and START condition			4.7	-	-	μs
t <sub>HD;STA</sub>	hold time (repeated) START condition	10 % of SDA to 90 % of SCL	<u>[1]</u>	4.7	-	-	μs
t <sub>HD;DAT</sub>	data hold time		[2]	300	-	-	ns
t <sub>SU;DAT</sub>	data set-up time			250	-	-	ns
t <sub>SU;STA</sub>	set-up time for a repeated START condition		[3]	250	-	-	ns
t <sub>SU;STO</sub>	set-up time for STOP condition			0.6	-	-	μs
t <sub>r</sub>	rise time of both SDA and SCL signals			-	-	300	ns
t <sub>f</sub>	fall time of both SDA and SCL signals			-	-	300	ns
t <sub>f(o)</sub>	output fall time			-	-	250	ns
t <sub>to(SMBus)</sub>	SMBus time-out time		[4]	25	-	35	ms

- [1] Delay from SDA START to first SCL HIGH-to-LOW transition.
- [2] Delay from SCL HIGH-to-LOW transition to SDA edges.
- [3] Delay from SCL LOW-to-HIGH transition to restart SDA.
- [4] LOW period to reset SMBus.

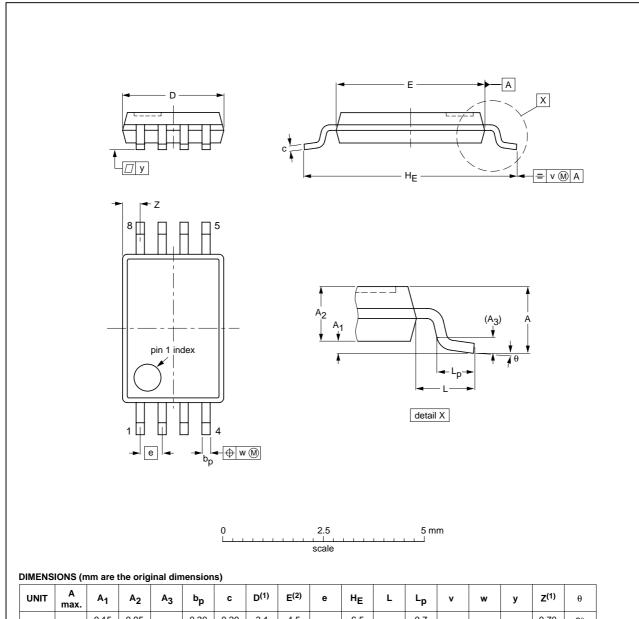


**SE98 NXP Semiconductors** 

## 12. Package outline

TSSOP8: plastic thin shrink small outline package; 8 leads; body width 4.4 mm

SOT530-1



UNIT	A max.	A <sub>1</sub>	A <sub>2</sub>	А3	bp	С	D <sup>(1)</sup>	E <sup>(2)</sup>	е	HE	L	Lp	v	w	у	Z <sup>(1)</sup>	θ
mm	1.1	0.15 0.05	0.95 0.85	0.25	0.30 0.19	0.20 0.13	3.1 2.9	4.5 4.3	0.65	6.5 6.3	0.94	0.7 0.5	0.1	0.1	0.1	0.70 0.35	8° 0°

- 1. Plastic or metal protrusions of 0.15 mm maximum per side are not included.
- 2. Plastic or metal protrusions of 0.25 mm maximum per side are not included.

OUTLINE		REFER	ENCES	EUROPEAN	ISSUE DATE	
VERSION	IEC	JEDEC	JEITA	PROJECTION	ISSUE DATE	
SOT530-1		MO-153			<del>00-02-24</del> 03-02-18	

Fig 20. Package outline SOT530-1 (TSSOP8)

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HVSON8: plastic thermal enhanced very thin small outline package; no leads; 8 terminals; body  $3 \times 3 \times 0.85 \text{ mm}$ 

SOT908-1

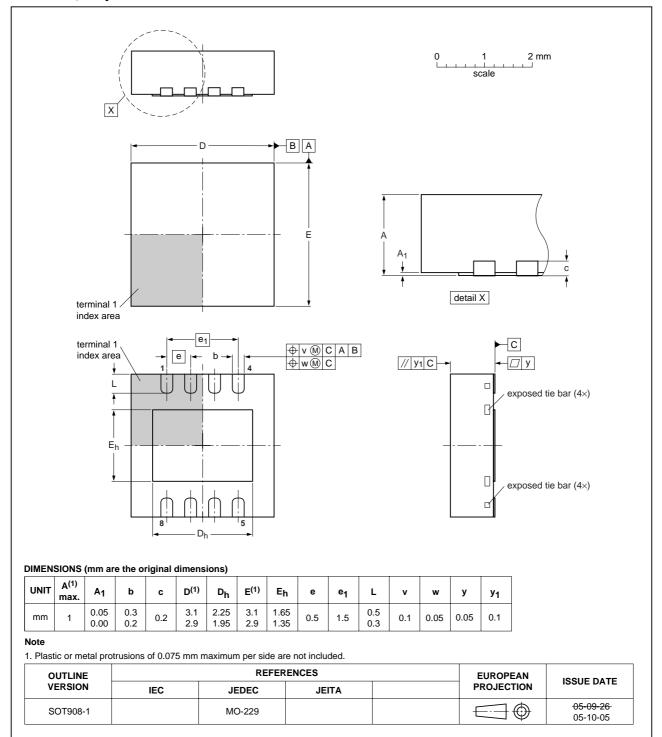


Fig 21. Package outline SOT908-1 (HVSON8)

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#### DDR memory module temp sensor, 3.3 V

## 13. Soldering of SMD packages

This text provides a very brief insight into a complex technology. A more in-depth account of soldering ICs can be found in Application Note *AN10365 "Surface mount reflow soldering description"*.

### 13.1 Introduction to soldering

Soldering is one of the most common methods through which packages are attached to Printed Circuit Boards (PCBs), to form electrical circuits. The soldered joint provides both the mechanical and the electrical connection. There is no single soldering method that is ideal for all IC packages. Wave soldering is often preferred when through-hole and Surface Mount Devices (SMDs) are mixed on one printed wiring board; however, it is not suitable for fine pitch SMDs. Reflow soldering is ideal for the small pitches and high densities that come with increased miniaturization.

### 13.2 Wave and reflow soldering

Wave soldering is a joining technology in which the joints are made by solder coming from a standing wave of liquid solder. The wave soldering process is suitable for the following:

- Through-hole components
- Leaded or leadless SMDs, which are glued to the surface of the printed circuit board

Not all SMDs can be wave soldered. Packages with solder balls, and some leadless packages which have solder lands underneath the body, cannot be wave soldered. Also, leaded SMDs with leads having a pitch smaller than ~0.6 mm cannot be wave soldered, due to an increased probability of bridging.

The reflow soldering process involves applying solder paste to a board, followed by component placement and exposure to a temperature profile. Leaded packages, packages with solder balls, and leadless packages are all reflow solderable.

Key characteristics in both wave and reflow soldering are:

- Board specifications, including the board finish, solder masks and vias
- · Package footprints, including solder thieves and orientation
- The moisture sensitivity level of the packages
- Package placement
- Inspection and repair
- Lead-free soldering versus SnPb soldering

### 13.3 Wave soldering

Key characteristics in wave soldering are:

- Process issues, such as application of adhesive and flux, clinching of leads, board transport, the solder wave parameters, and the time during which components are exposed to the wave
- Solder bath specifications, including temperature and impurities

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#### DDR memory module temp sensor, 3.3 V

## 13.4 Reflow soldering

Key characteristics in reflow soldering are:

- Lead-free versus SnPb soldering; note that a lead-free reflow process usually leads to higher minimum peak temperatures (see <u>Figure 22</u>) than a SnPb process, thus reducing the process window
- Solder paste printing issues including smearing, release, and adjusting the process window for a mix of large and small components on one board
- Reflow temperature profile; this profile includes preheat, reflow (in which the board is heated to the peak temperature) and cooling down. It is imperative that the peak temperature is high enough for the solder to make reliable solder joints (a solder paste characteristic). In addition, the peak temperature must be low enough that the packages and/or boards are not damaged. The peak temperature of the package depends on package thickness and volume and is classified in accordance with Table 28 and 29

Table 28. SnPb eutectic process (from J-STD-020C)

Package thickness (mm)	Package reflow temperature (°C)					
	Volume (mm <sup>3</sup> )					
	< 350	≥ 350				
< 2.5	235	220				
≥ 2.5	220	220				

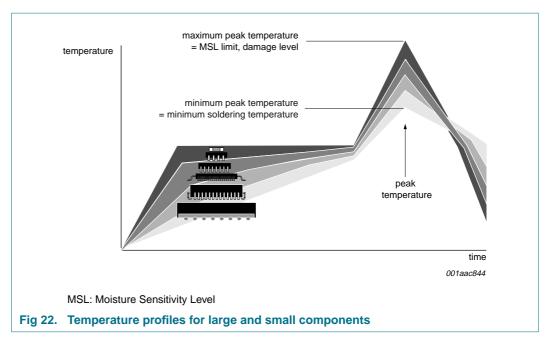
Table 29. Lead-free process (from J-STD-020C)

Package thickness (mm)	Package reflow temperature (°C)							
	Volume (mm³)							
	< 350	350 to 2000	> 2000					
< 1.6	260	260	260					
1.6 to 2.5	260	250	245					
> 2.5	250	245	245					

Moisture sensitivity precautions, as indicated on the packing, must be respected at all times.

Studies have shown that small packages reach higher temperatures during reflow soldering, see Figure 22.

### DDR memory module temp sensor, 3.3 V



For further information on temperature profiles, refer to Application Note *AN10365* "Surface mount reflow soldering description".

## 14. Abbreviations

Table 30. Abbreviations

A	Paradiation
Acronym	Description
ADC	Analog-to-Digital Converter
ARA	Alert Response Address
CDM	Charged Device Model
CMOS	Complementary Metal-Oxide Semiconductor
DIMM	Dual In-line Memory Module
DRAM	Dynamic Random Access Memory
HBM	Human Body Model
I <sup>2</sup> C-bus	Inter Integrated Circuit bus
LSB	Least Significant Bit
MM	Machine Model
MSB	Most Significant Bit
SO-DIMM	Small Outline Dual In-line Memory Module
POR	Power-On Reset
SMBus	System Management Bus
SPD	Serial Presence Detect

## DDR memory module temp sensor, 3.3 V

## 15. Revision history

## Table 31. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes				
SE98_4	20090202	Product data sheet	-	SE98_3				
Modifications:	<ul> <li>Changed data sheet descriptive title from "SO-DIMM SMBus/I<sup>2</sup>C-bus temperature sensor" to "DDR memory module temp sensor, 3.3 V"</li> </ul>							
	<ul> <li>Section 1 "General description", first sentence: changed from "-20 °C to +125 °C" to "-40 °C to +125 °C"</li> </ul>							
	<ul> <li>Section 2.2 "Temperature sensor features", last bullet item changed from "-20 °C to +125 °C" to "-40 °C to +125 °C"</li> </ul>							
	Section 7.3 "EVENT output condition" re-written							
	<ul> <li>Added <u>Section</u></li> </ul>	n 7.10 "Hot plugging"						
	<ul> <li>Table 7 "Capa</li> </ul>	bility register (address 00h)	bit description":					
	<ul><li>description</li></ul>	of symbol TRES: appende	d "(11-bit)"					
	ical Trips capability" to "has							
<ul> <li><u>Table 9 "Configuration register (address 01h) bit description"</u>: description of bit 2, CVO, re</li> </ul>								
	Table 10 "Hysteresis enable":							
	<ul> <li>added 2 right-most columns "Critical Alarm Window Bit (bit 15)"</li> </ul>							
	<ul><li>"T<sub>th(low)</sub>" replaced with "T<sub>trip(l)</sub>"</li></ul>							
	<ul><li>"T<sub>th(high)</sub>" replaced with "T<sub>trip(u)</sub>"</li></ul>							
	<ul><li>– "hysteresis" replaced with "T<sub>hys</sub>"</li></ul>							
		emperature format": added	4 <sup>th</sup> paragraph and <u>Table 1</u>	<u> 1</u>				
	• Table 25 "Characteristics":							
	<ul><li>changed d</li><li>+125 °C"</li></ul>	escriptive line below table ti	tle from " $T_{amb} = -20  ^{\circ}C$ to	$+125  ^{\circ}\text{C"} \text{ to "T}_{\text{amb}} = -40  ^{\circ}\text{C to}$				
	- symbol $T_{lim(acc)}$ , condition " $T_{amb} = -20$ °C to +125 °C" changed to " $T_{amb} = -40$ °C to +125 °C"							
		Bus DC characteristics": cha C to +120 °C" to "T <sub>amb</sub> = -4		ow table title from				
		Bus AC characteristics": cha C to +120 °C" to "T <sub>amb</sub> = -4		ow table title from				
SE98_3	20080404	Product data sheet	-	SE98_2				
SE98_2	20080107	Product data sheet	-	SE98_1				
SE98_1 (9397 750 14649)	20060510	Product data sheet	-	-				

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## 16. Legal information

#### 16.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
- [3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL <a href="http://www.nxp.com">http://www.nxp.com</a>.

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36 of 39

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## DDR memory module temp sensor, 3.3 V

## 18. Contents

1	General description	. 1
2	Features	
2.1	General features	. 2
2.2	Temperature sensor features	. 2
3	Applications	. 2
4	Ordering information	. 2
5	Block diagram	. 3
6	Pinning information	. 4
6.1	Pinning	. 4
6.2	Pin description	. 4
7	Functional description	. 5
7.1	Serial bus interface	. 5
7.2	Slave address	
7.3	EVENT output condition	. 6
7.3.1	EVENT pin output voltage levels and	
	resistor sizing	
7.3.2	EVENT thresholds	
7.3.2.1	Alarm window	
7.3.2.2 7.3.3	Critical trip	
7.3.3.1	Comparator mode	
7.3.3.1	Interrupt mode	
7.4	Conversion rate	10
7.5	Power-up default condition	10
7.6	Device initialization	10
7.7	SMBus time-out	11
7.8	SMBus Alert	11
7.9	SMBus/I <sup>2</sup> C-bus interface	12
7.10	Hot plugging	14
8	Register descriptions	15
8.1	Register overview	15
8.2	Capability register (00h, 16-bit read-only)	16
8.3	Configuration register (01h, 16-bit read/write)	17
8.4	Temperature format	20
8.5	Temperature Trip Point registers	21
8.5.1	Upper Boundary Alarm Trip register	24
8.5.2	(16-bit read/write)	21
0.5.2	(16-bit read/write)	22
8.5.3	Critical Alarm Trip register (16-bit read/write).	22
8.6	Temperature register (16-bit read-only)	23
8.7	Manufacturer's ID register (16-bit read-only) .	23
8.8	Device ID register	24
8.9	SMBus register	24
9	Application design-in information	25
9.1	SE98 in memory module application	25

9.2	Layout consideration	26
9.3	Thermal considerations	26
10	Limiting values	26
11	Characteristics	27
12	Package outline	30
13	Soldering of SMD packages	32
13.1	Introduction to soldering	32
13.2	Wave and reflow soldering	32
13.3	Wave soldering	32
13.4	Reflow soldering	33
14	Abbreviations	34
15	Revision history	35
16	Legal information	36
16.1	Data sheet status	36
16.2	Definitions	36
16.3	Disclaimers	36
16.4	Trademarks	36
17	Contact information	36
18	Contents	37
10	Contents	31

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